

▼ Simple Drive Requirement

▼ Easy for DC/DC Buck

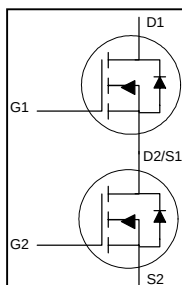
Converter Application

▼ RoHS Compliant & Halogen-Free

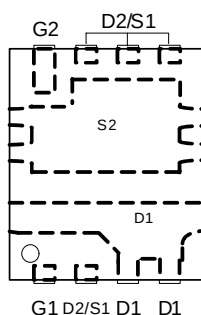
Description

XSemi MOSFETs provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

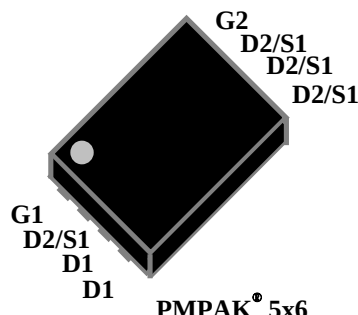
The control MOSFET (CH-1) and synchronous MOSFET (CH-2) co-package for synchronous buck converters. The package provide optimal efficiency with low stray inductance and very low on-resistance.



CH-1	BV_{DSS}	30V
	$R_{DS(ON)}$	5m Ω
CH-2	BV_{DSS}	30V
	$R_{DS(ON)}$	1.9m Ω



PMPAK 5x6



PMPAK[®] 5x6

Absolute Maximum Ratings@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Rating		Units
		CH-1	CH-2	
V_{DS}	Drain-Source Voltage	30	30	V
V_{GS}	Gate-Source Voltage	+20	+20	V
$I_D@T_C=25^{\circ}C$	Drain Current (Package Limited)	55	85	A
$I_D@T_A=25^{\circ}C$	Drain Current , V_{GS} @ 10V ³	16	27	A
$I_D@T_A=70^{\circ}C$	Drain Current , V_{GS} @ 10V ³	12.8	21.8	A
I_{DM}	Pulsed Drain Current ¹	120	240	A
$P_D@T_A=25^{\circ}C$	Total Power Dissipation ³	2.08	2.27	W
E_{AS}	Single Pulse Avalanche Energy ⁶	18	32	mJ
T_{STG}	Storage Temperature Range	-55 to 150		°C
T_J	Operating Junction Temperature Range	-55 to 150		°C

Thermal Data

Symbol	Parameter	Rating		Units
		CH-1	CH-2	
Rthj-c	Maximum Thermal Resistance, Junction-case	5	3	°C/W
Rthj-t	Maximum Thermal Resistance, Junction-top	15	9	°C/W
Rthj-a	Maximum Thermal Resistance, Junction-ambient ³	60	55	°C/W
Rthj-a	Maximum Thermal Resistance, Junction-ambient ⁴	130	120	°C/W

CH-1 Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	-	-	V
V _{DSt}	Drain-Source Breakdown Voltage ⁷ (transient)	V _{GS} =0V, I _{AS} =60A, t _{transient} ≤ 50ns	36	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =16A	-	3.5	5	mΩ
		V _{GS} =4.5V, I _D =8A	-	5.5	8	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	1.3	1.7	2.2	V
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =16A	-	55	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =24V, V _{GS} =0V	-	-	10	uA
I _{GSS}	Gate-Source Leakage	V _{GS} = ±20V, V _{DS} =0V	-	-	+0.1	uA
Q _{g(10V)}	Total Gate Charge ⁵	I _D =16A V _{DS} =15V	-	19	30.4	nC
Q _{g(4.5V)}	Total Gate Charge ⁵		-	9	14.4	nC
Q _{gs}	Gate-Source Charge ⁵		-	4	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge ⁵		-	3	-	nC
t _{d(on)}	Turn-on Delay Time ⁵	V _{DS} =15V	-	8	-	ns
t _r	Rise Time ⁵	I _D =16A	-	54	-	ns
t _{d(off)}	Turn-off Delay Time ⁵	R _G =3Ω	-	18	-	ns
t _f	Fall Time ⁵	V _{GS} =10V	-	3	-	ns
C _{iss}	Input Capacitance ⁵	V _{GS} =0V	-	1070	1712	pF
C _{oss}	Output Capacitance ⁵	V _{DS} =15V	-	550	-	pF
C _{rss}	Reverse Transfer Capacitance ⁵	f=1.0MHz	-	30	-	pF
R _g	Gate Resistance	f=1.0MHz	-	2.2	4.4	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =16A, V _{GS} =0V	-	-	1.2	V
t _{rr}	Reverse Recovery Time ⁵	I _S =16A, V _{GS} =0V dI/dt=100A/μs	-	23	-	ns
Q _{rr}	Reverse Recovery Charge ⁵		-	13	-	nC

CH-2 Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	-	-	V
V _{DSt}	Drain-Source Breakdown Voltage ⁷ (transient)	V _{GS} =0V, I _{AS} =80A, t _{transient} ≤ 50ns	36	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =20A	-	1.4	1.9	mΩ
		V _{GS} =4.5V, I _D =12A	-	2.4	3.1	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	1.3	1.7	2.2	V
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =20A	-	100	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =24V, V _{GS} =0V	-	-	10	uA
I _{GSS}	Gate-Source Leakage	V _{GS} = ±20V, V _{DS} =0V	-	-	±0.1	uA
Q _{g(10V)}	Total Gate Charge ⁵	I _D =20A V _{DS} =15V	-	40	64	nC
Q _{g(4.5V)}	Total Gate Charge ⁵		-	19	30.4	nC
Q _{gs}	Gate-Source Charge ⁵		-	9	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge ⁵		-	5	-	nC
t _{d(on)}	Turn-on Delay Time ⁵	V _{DS} =15V	-	10	-	ns
t _r	Rise Time ⁵	I _D =20A	-	47	-	ns
t _{d(off)}	Turn-off Delay Time ⁵	R _G =3Ω	-	28	-	ns
t _f	Fall Time ⁵	V _{GS} =10V	-	6	-	ns
C _{iss}	Input Capacitance ⁵	V _{GS} =0V	-	2450	3920	pF
C _{oss}	Output Capacitance ⁵	V _{DS} =15V	-	1450	-	pF
C _{rss}	Reverse Transfer Capacitance ⁵	f=1.0MHz	-	50	-	pF
R _g	Gate Resistance	f=1.0MHz	-	1.2	2.4	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =20A, V _{GS} =0V	-	-	1.2	V
t _{rr}	Reverse Recovery Time ⁵	I _S =20A, V _{GS} =0V dI/dt=100A/μs	-	40	-	ns
Q _{rr}	Reverse Recovery Charge ⁵		-	38	-	nC

Notes:

1. Pulse width limited by Max. junction temperature.
2. Pulse test
3. Surface mounted on 1 in² copper pad of FR4 board, on steady-state
4. Surface mounted on Min. copper pad of FR4 board, on steady-state
5. Guaranteed by design.
6. Starting T_j=25°C, V_{DD}=30V, L=0.01mH, R_G=25Ω, V_{GS}=10V
7. T_j=25°C. Expected voltage stress during 100% EAS test. Production datalog is not available.

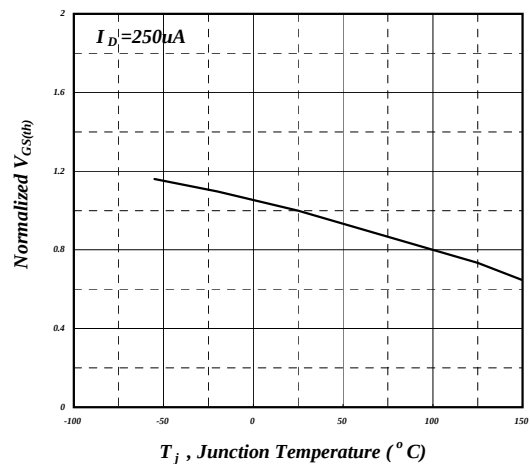
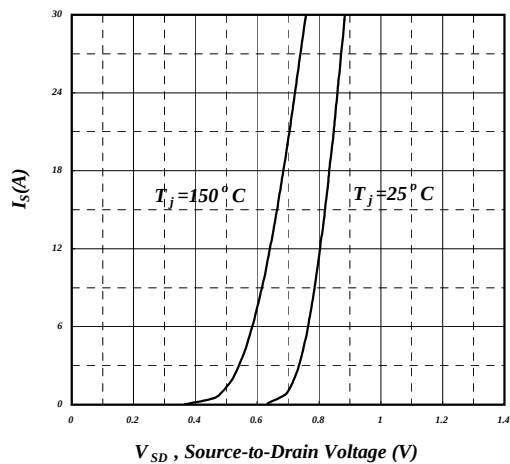
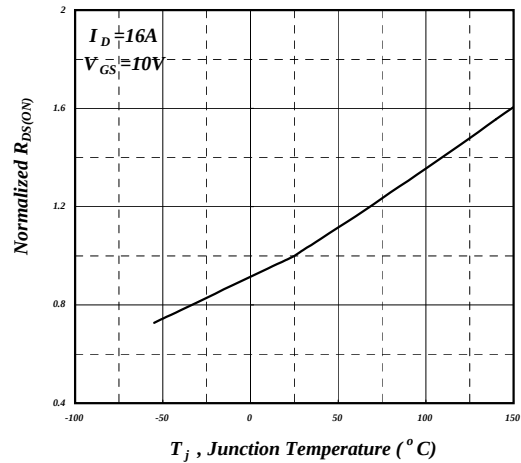
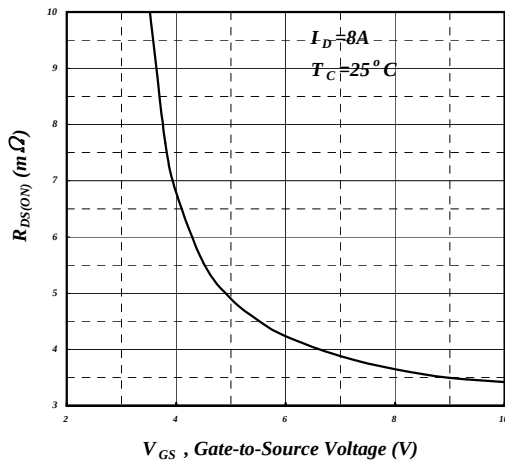
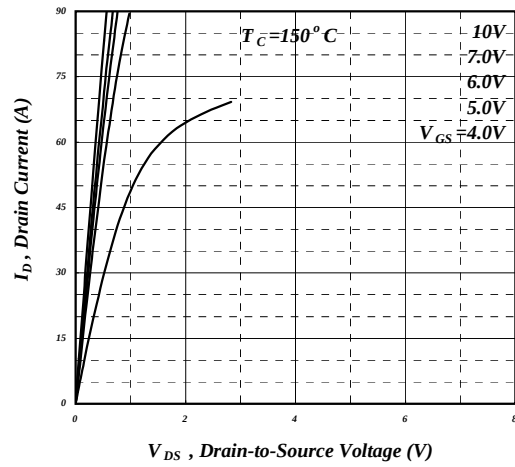
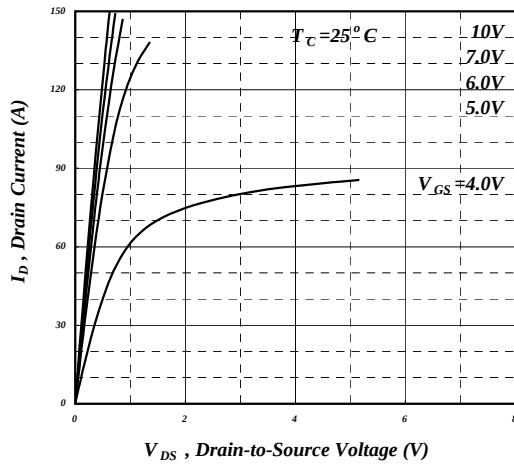
THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT, AUTOMOTIVE OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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Channel-1



Channel-1

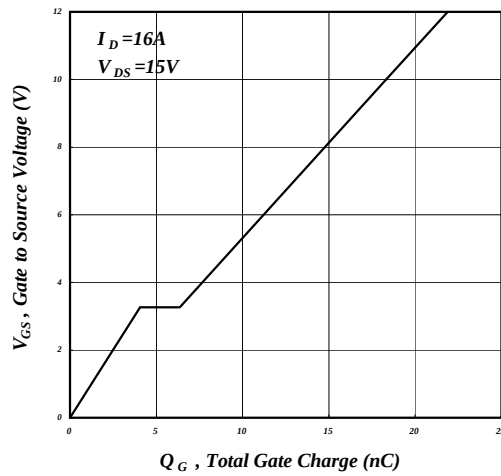


Fig 7. Gate Charge Characteristics

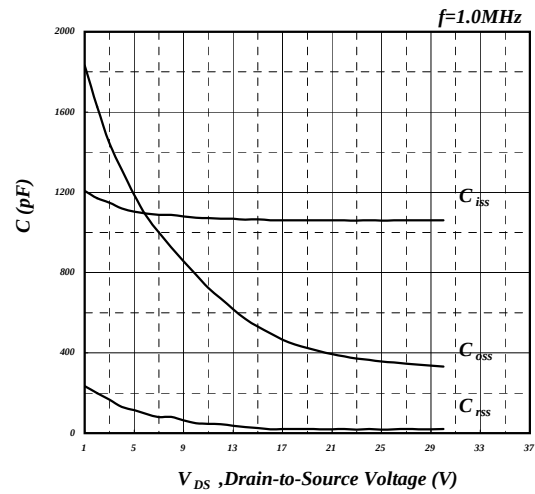


Fig 8. Typical Capacitance Characteristics

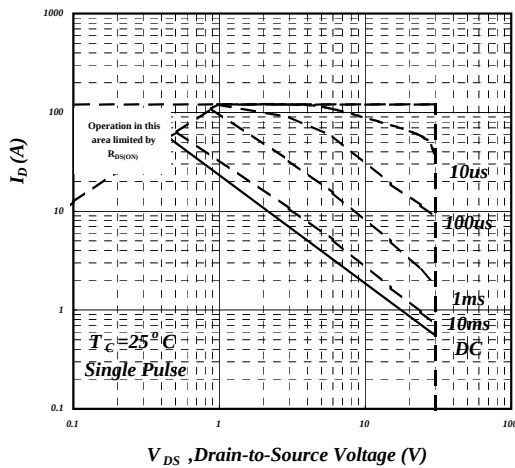


Fig 9. Maximum Safe Operating Area

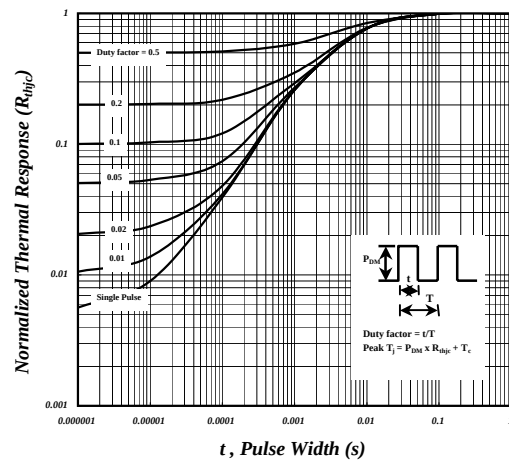


Fig 10. Effective Transient Thermal Impedance

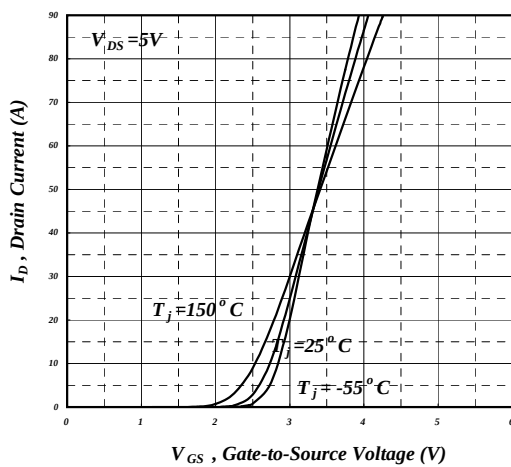


Fig 11. Transfer Characteristics

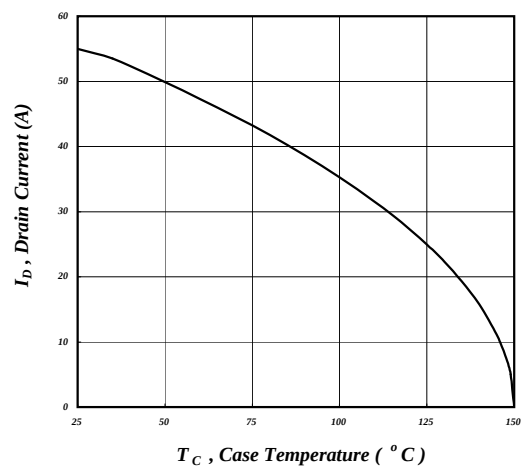


Fig 12. Drain Current v.s. Case Temperature

Channel-1

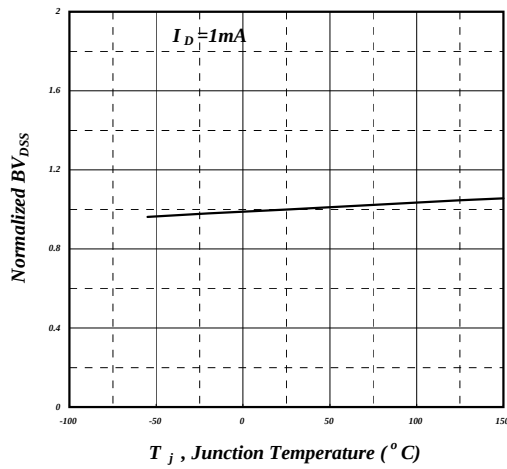


Fig 13. Normalized BV_{DSS} v.s. Junction Temperature

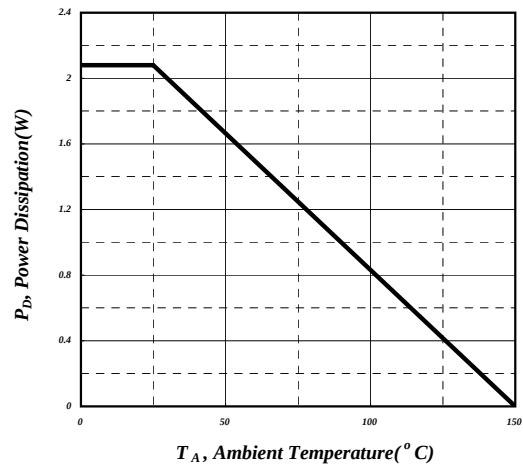


Fig 14. Total Power Dissipation

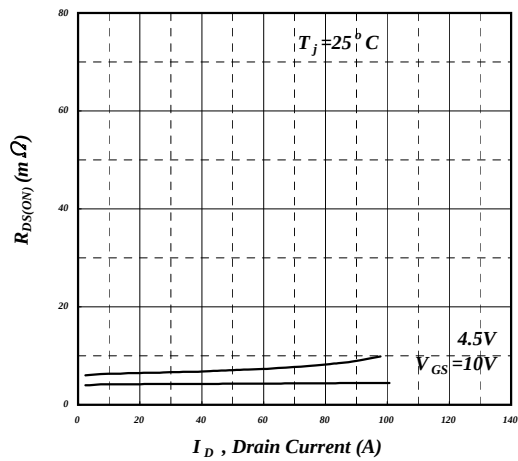


Fig 15. Typ. Drain-Source on State Resistance

Channel-2

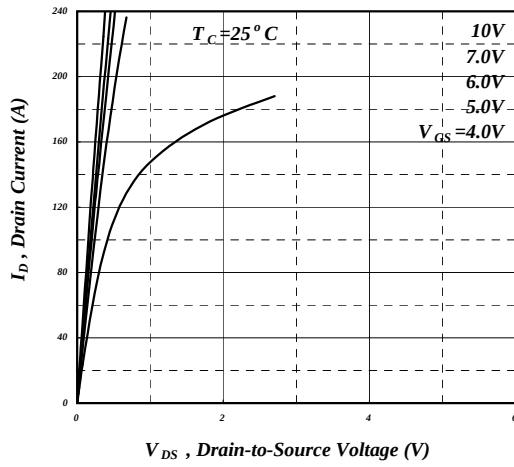


Fig 1. Typical Output Characteristics

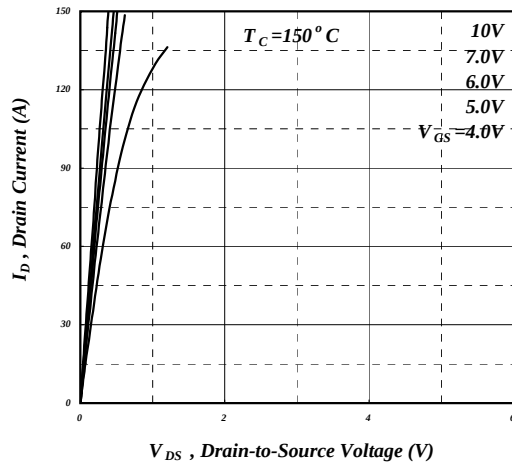


Fig 2. Typical Output Characteristics

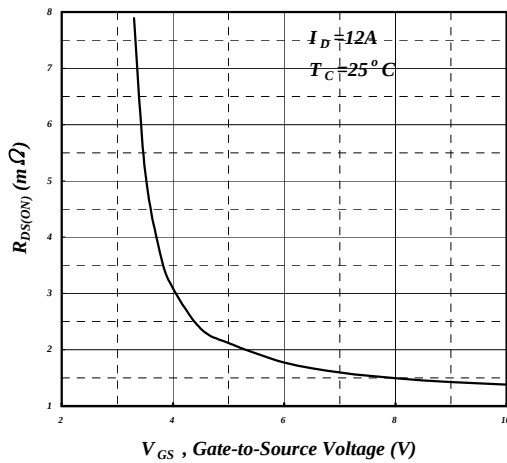
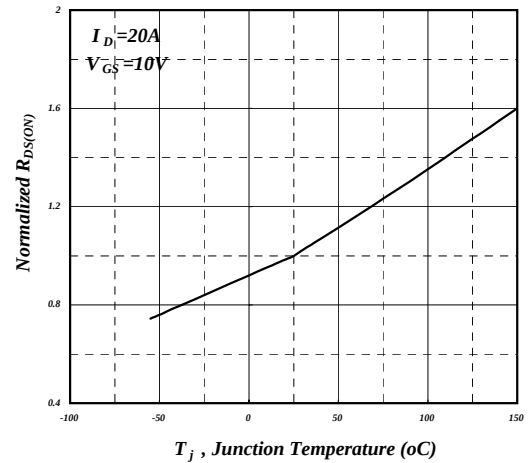
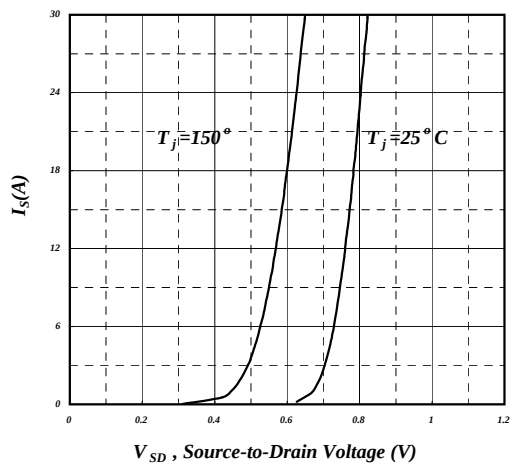


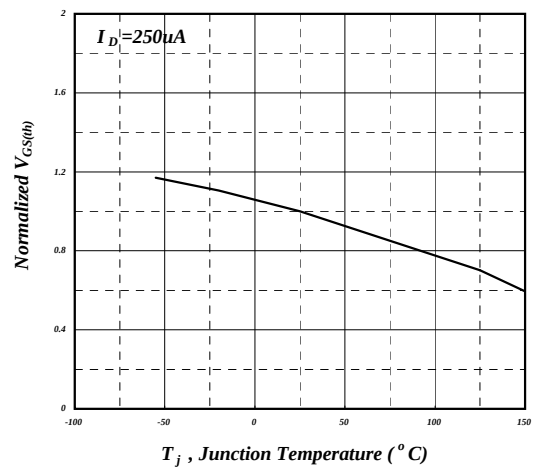
Fig 3. On-Resistance v.s. Gate Voltage



**Fig 4. Normalized On-Resistance
v.s. Junction Temperature**



**Fig 5. Forward Characteristic of
Reverse Diode**



**Fig 6. Gate Threshold Voltage v.s.
Junction Temperature**

Channel-2

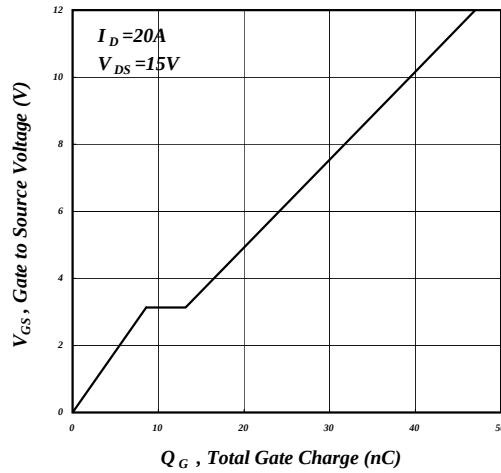


Fig 7. Gate Charge Characteristics

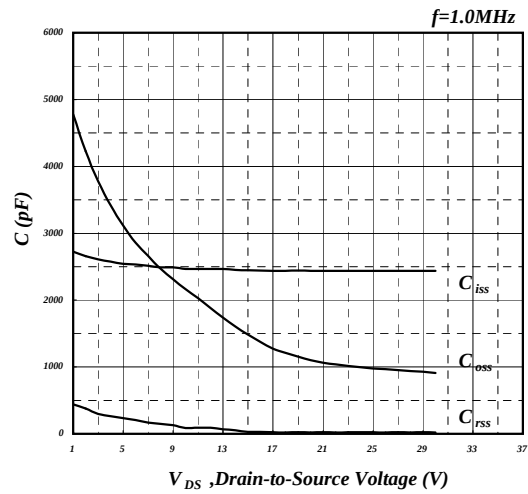


Fig 8. Typical Capacitance Characteristics

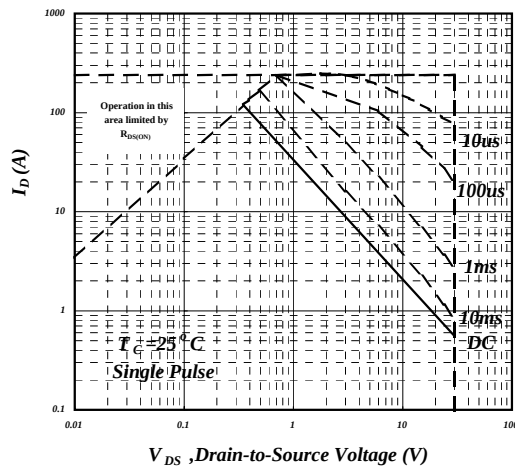


Fig 9. Maximum Safe Operating Area

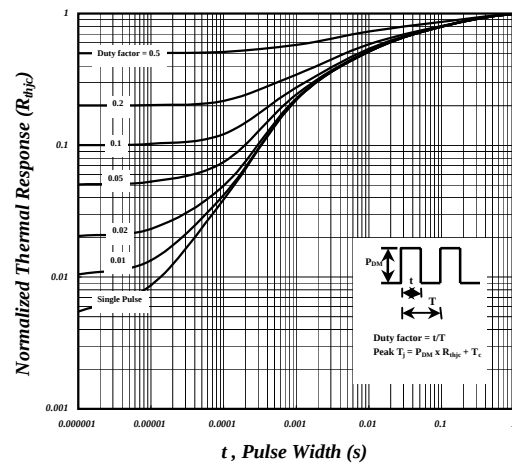


Fig 10. Effective Transient Thermal Impedance

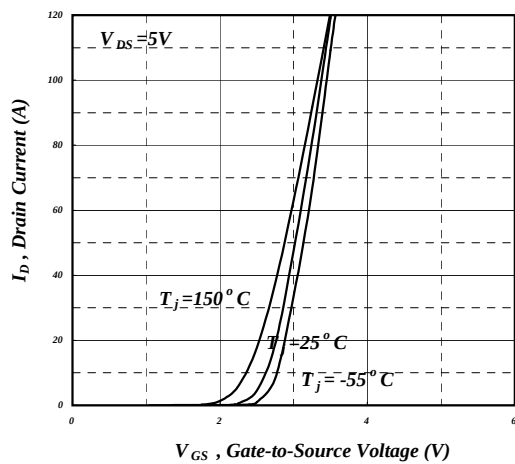


Fig 11. Transfer Characteristics

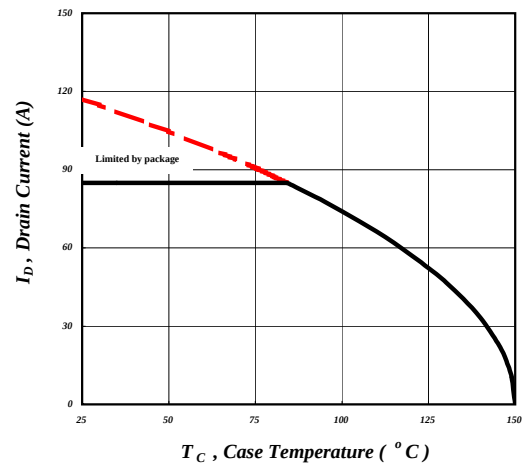


Fig 12. Drain Current v.s. Case Temperature

Channel-2

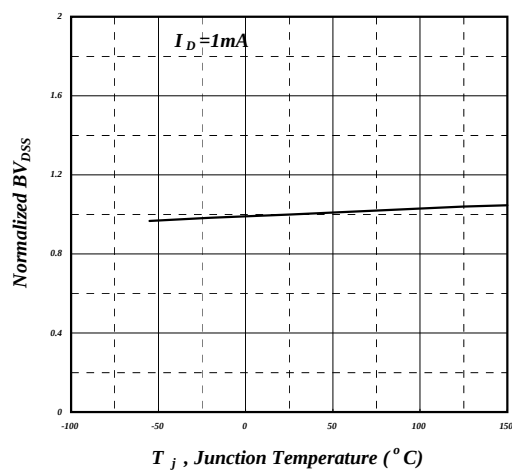


Fig 13. Normalized BV_{DSS} v.s. Junction Temperature

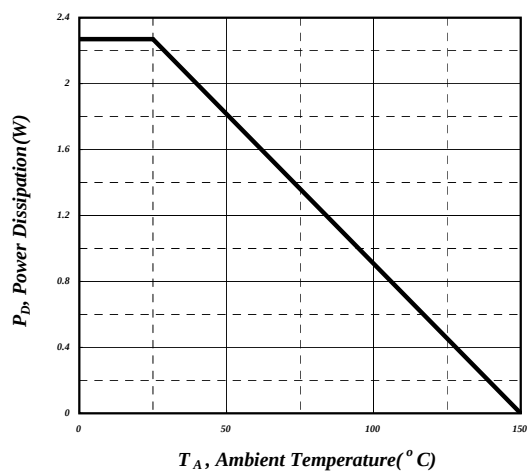


Fig 14. Total Power Dissipation

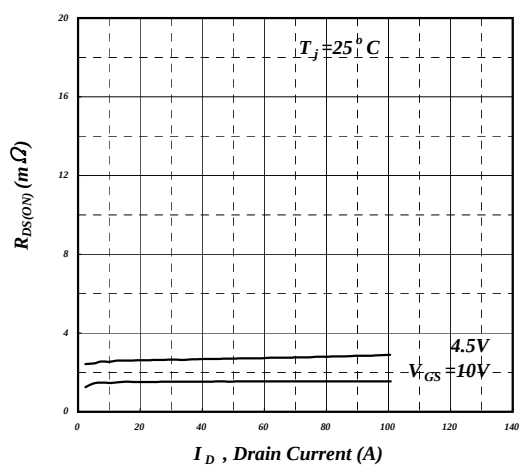
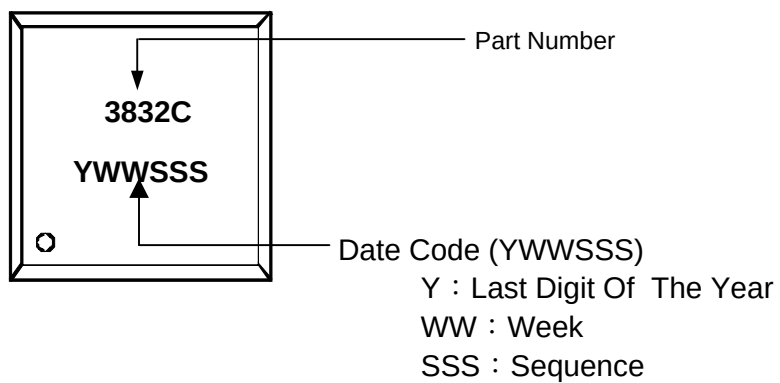
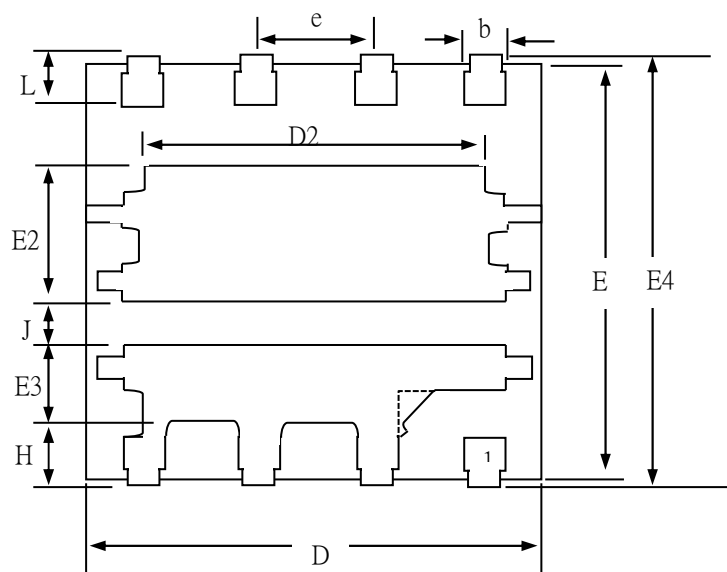


Fig 15. Typ. Drain-Source on State Resistance

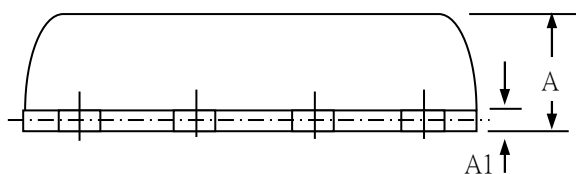
MARKING INFORMATION



Package Outline : PMPAK 5x6 (DUD)



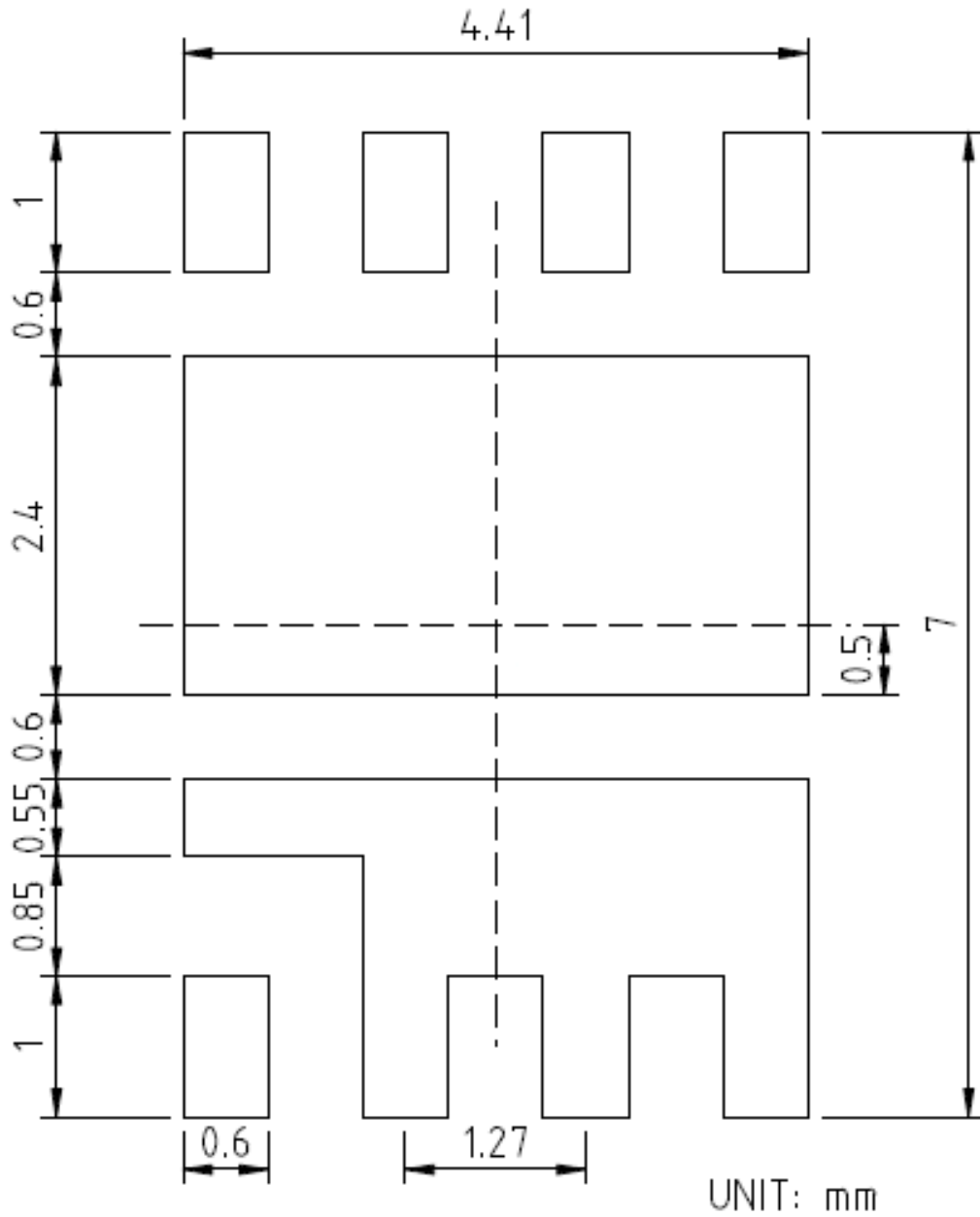
BACKSIDE VIEW



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	0.90	1.00	1.10
b	0.33	0.42	0.51
A1	0.20	0.25	0.30
D	4.80	4.90	5.00
D2	3.61	3.79	3.96
E4	5.90	6.03	6.15
E	5.70	5.75	5.80
E2	2.02	2.22	2.42
E3	0.94	1.18	1.42
e	1.27BSC		
J	0.40	0.50	0.60
H	0.48	0.58	0.68
L	0.38	0.55	0.71

- 1.All dimension are in millimeters.
- 2.Dimension does not include burrs and mold flash/protrusions.
- 3.The outline schematic is not to scale and slightly different from the actual product appearance.

PMPAK 5x6 (DUD) FOOTPRINT :



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